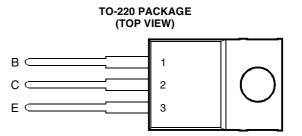
BDW73, BDW73A, BDW73B, BDW73C, BDW73D NPN SILICON POWER DARLINGTONS

BOURNS®

- Designed for Complementary Use with BDW74, BDW74A, BDW74B, BDW74C and BDW74D
- 80 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Minimum h_{FE} of 750 at 3V, 3 A

This series is obsolete and not recommended for new designs.



Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT		
	BDW73		45		
	BDW73A		60		
Collector-base voltage ($I_E = 0$)	BDW73B	V _{CBO}	80	V	
	BDW73C		100		
	BDW73D		120		
	BDW73		45		
Collector-emitter voltage ($I_B = 0$) (see Note 1)	BDW73A		60		
	BDW73B	V _{CEO}	80	V	
	BDW73C		100		
	BDW73D		120		
Emitter-base voltage		V _{EBO}	5	V	
Continuous collector current		Ι _C	8	А	
Continuous base current	I _B	0.3	А		
Continuous device dissipation at (or below) 25°C case temperature (see Note 2	P _{tot}	80	W		
Continuous device dissipation at (or below) 25°C free air temperature (see Note	P _{tot}	2	W		
Unclamped inductive load energy (see Note 4)	½Ll _C ²	75	mJ		
Operating junction temperature range	Тj	-65 to +150	°C		
Operating temperature range	T _{stg}	-65 to +150	°C		
Operating free-air temperature range	T _A	-65 to +150	°C		

NOTES: 1. These values apply when the base-emitter diode is open circuited.

2. Derate linearly to 150°C case temperature at the rate of 0.64 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)} = 5$ mA, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V.

PRODUCT INFORMATION

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS				MIN	ТҮР	MAX	UNIT
	Collector-emitter				BDW73 BDW73A	45 60			
V(DD)OFO	breakdown voltage	I _C = 30 mA	$I_B = 0$	(see Note 5)	BDW73B	80			V
					BDW73C	100			
					BDW73D	120			
		V _{CE} = 30 V	$I_B = 0$		BDW73			0.5	
	Collector-emitter	V _{CE} = 30 V	$I_B = 0$		BDW73A			0.5	
I _{CEO}	cut-off current	$V_{CE} = 40 V$	$I_B = 0$		BDW73B			0.5	mA
	cut-on current	$V_{CE} = 50 V$	$I_B = 0$		BDW73C			0.5	
		$V_{CE} = 60 V$	$I_B = 0$		BDW73D			0.5	
I _{CBO}		V _{CB} = 45 V	I _E = 0		BDW73			0.2	
		$V_{CB} = 60 V$	$I_E = 0$		BDW73A			0.2	
		V _{CB} = 80 V	$I_E = 0$		BDW73B			0.2	
		V _{CB} = 100 V	$I_E = 0$		BDW73C			0.2	
	Collector cut-off	V _{CB} = 120 V	$I_E = 0$		BDW73D			0.2	mA
	current	V _{CB} = 45 V	$I_E = 0$	$T_{C} = 150^{\circ}C$	BDW73			5	110.
			$I_E = 0$	$T_C = 150^{\circ}C$	BDW73A			5	
			$I_E = 0$	T _C = 150°C	BDW73B			5	
		V _{CB} = 100 V	$I_E = 0$	T _C = 150°C	BDW73C			5	
		V _{CB} = 120 V	$I_E = 0$	T _C = 150°C	BDW73D			5	
I _{EBO}	Emitter cut-off current	V _{EB} = 5 V	I _C = 0					2	mA
h	Forward current	V _{CE} = 3 V	l _C = 3 A	(see Notes 5 and 6)		750		20000	
h _{FE}	transfer ratio	V _{CE} = 3 V	l _C = 8 A	(see Notes 5 and 6)		100			
V _{BE(on)}	Base-emitter voltage	V _{CE} = 3V	I _C = 3 A	(see Notes 5 and 6)				2.5	V
V _{CE(sat)}	Collector-emitter saturation voltage	$I_{\rm B} = 12 \text{ mA}$ $I_{\rm B} = 80 \text{ mA}$	$I_{\rm C} = 3$ A $I_{\rm C} = 8$ A	(see Notes 5 and 6)				2.5 4	V
V_{EC}	Parallel diode forward voltage	I _E = 8 A	I _B = 0					3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, $t_0 = 300 \ \mu$ s, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER			ТҮР	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1.56	°C/W
R _{θJA}	Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

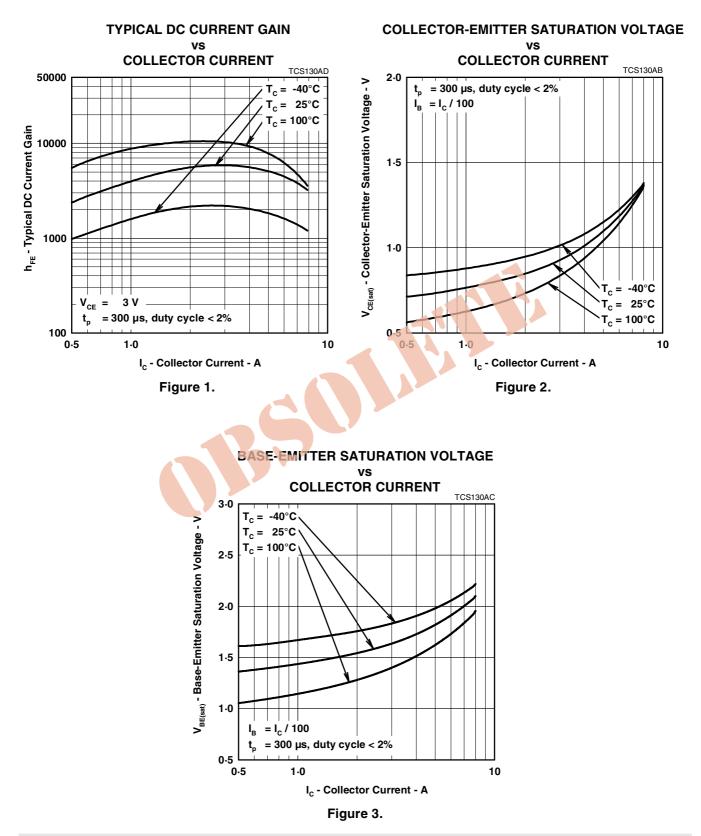
PARAMETER	TEST CONDITIONS [†]				ТҮР	MAX	UNIT
t _{on} Turn-on time	I _C = 3 A	$I_{B(on)} = 12 \text{ mA}$	$I_{B(off)} = -12 \text{ mA}$		1		μs
t _{off} Turn-off time	$V_{BE(off)} = -3.5 V$	$R_L = 10 \ \Omega$	$t_p = 20 \ \mu s, \ dc \le 2\%$		5		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

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BDW73, BDW73A, BDW73B, BDW73C, BDW73D NPN SILICON POWER DARLINGTONS

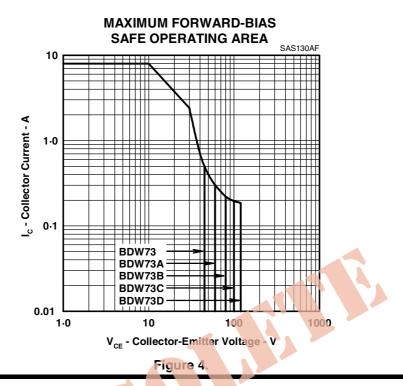
TYPICAL CHARACTERISTICS



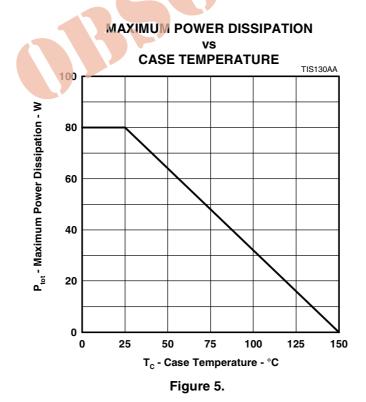
PRODUCT INFORMATION

AUGUST 1978 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION



PRODUCT INFORMATION